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Contents

PREFACE	xvii
PART I: GROWTH AND STRUCTURE	
SURFACE REACTIONS IN DISCHARGE AND CVD DEPOSITION OF SILANE Alan Gallagher	3
REACTIVE DEPOSITION OF a-SILICON AND Si-BASED ALLOYS J. Hanna, S. Oda, H. Shibata, H. Shirai, A. Miyauchi, A. Tanabe, K. Fukuda, T. Ohtoshi, O. Tokuhira, H. Nguyen and I. Shimizu	11
NOVEL PROPERTIES OF a-Si:H PREPARED BY DUAL ION BEAM SPUTTERING H. Windischmann, R.W. Collins and J.M. Cavese	17
CONTROL OF a-Si:H FILM PROPERTIES BY PHOTO-ASSISTED PLASMA CVD Nobuhiro Fukuda, Kenji Miyachi, Hirofumi Tanaka, Takashi Igarashi and Sadaaki Yamamoto	25
HYDROGENATED AMORPHOUS SILICON THIN-FILM DEPOSITON BY DIRECT PHOTO-ENHANCED DECOMPOSITION OF SILANE USING AN INTERNAL HYDROGEN DISCHARGE LAMP P.A. Robertson and W.I. Milne	31
PROPERTIES OF a-Si:H AND a-SiGe:H FILMS DEPOSITED BY PHOTO-ASSISTED CVD R.E. Rocheleau, S.C. Jackson, S.S. Hegedus and B.N. Baron	37
HYDROGENATED AMORPHOUS SILICON ALLOYS PREPARED BY CVD OF HIGHER SILANES Masud Akhtar and Herbert A. Weakliem	43
PROPERTIES OF AMORPHOUS SILICON FILMS DEPOSITED AT RATES HIGHER THAN 1 $\mu\text{m}/\text{MIN}$ T.L. Chu, Shirley S. Chu, S.T. Ang, A. Duong and Y.X. Han	49
COMPARISON STUDIES OF HYDROGENATED AMORPHOUS SILICON FILMS PREPARED FROM SILANE-HYDROGEN AND SILANE-HELIUM MIXTURES R.I. Patel, D.J., Olsen, J.R. Shirck and N.T. Tran	55
A COMPARATIVE STUDY OF HYDROGENATED AMORPHOUS SILICON FILMS PREPARED BY RF SPUTTERING IN He/H ₂ , Ar/H ₂ AND Xe/H ₂ MIXTURES Mark L. Albers, H.R. Shanks and J. Shinar	59
PROPERTIES OF POST-HYDROGENATED AMORPHOUS AND MICROCRYSTALLINE GERMANIUM FILMS James R. Woodyard, J. Gonzalez-Hernandez, R.T. Young and J. Piontkowski	65
TEM CHARACTERIZATION OF SOLID-PHASE EPITAXY IN AMORPHIZED POLYSILICON P.-H. Chang and R. Sundaresan	71
BOND ANGLE DISORDER IN TETRAHEDRALLY BONDED AMORPHOUS SILICON C.K. Wong and G. Lucovsky	77

MULTIPLE QUANTUM NMR STUDY OF HYDROGEN CLUSTERING IN AMORPHOUS SILICON Karen K. Gleason, J. Baum, A.N. Garroway, A. Pines and J.A. Reimer	83
ANNEALING EFFECTS ON DEUTERIUM IN a-Si:D V.P. Bork, P.A. Fedders, D.J. Leopold, R.E. Norberg, J.B. Boyce and J.C. Knights	89
PART II: ELECTRONIC STRUCTURE AND DEFECTS	
AB-INITIO THEORY OF DEFECT STRUCTURE IN a-Si iH Yaneer Bar-Yam and J.D. Joannopoulos	97
ELECTRONIC STRUCTURE OF DIVALENT DEFECTS IN TETRAHEDRALLY BONDED AMORPHOUS MATERIALS S.Y. Lin, G. Lucovsky, S. Guha and J.S. Payson	107
INADEQUACY OF THE CONVENTIONAL VIEW OF HYDROGENATED AMORPHOUS SILICON D. Adler, M. Silver, M.P. Shaw and V. Cannella	113
ELECTRONIC TRANSPORT IN HYDROGENATED AMORPHOUS SILICON M. Silver, D. Adler, M.P. Shaw, V. Cannella and J. McGill	119
THE DANGLING BOND IN UNDOPED AMORPHOUS HYDROGENATED SILICON: TRAP OR RECOMBINATION CENTER? M.A. Parker, K.A. Conrad and E.A. Schiff	125
STUDY OF TRAPPING AND RECOMBINATION IN a-Si:H BY MEANS OF INFRARED ENHANCEMENT SPECTRA OF PHOTOCONDUCTIVITY Wu Wenhao, Qui Changhua, Zhao Shifu and Han Daxing	131
INFLUENCE OF PREPARATION CONDITIONS ON CHARGE CARRIER DYNAMICS IN a-Si:H DETERMINED BY AN IN-SITU TECHNIQUE A. Werner and M.Kunst	137
THE PHOTOCONDUCTIVITY EXPONENT FOR RECOMBINATION AT DANGLING BONDS IN a-Si:H F. Vaillant and D. Jousse	143
ANALYTICAL DETERMINATION OF GENERATION-RECOMBINATION RATE IN AMORPHOUS SILICON Joze Furlan and Slavko Amon	149
ROOM TEMPERATURE LIGHT INDUCED ELECTRON SPIN RESONANCE IN UNDOPED HYDROGENATED AMORPHOUS SILICON (a-Si:H) R. Pandya, S. Zafar and E.A. Schiff	155
INTERPRETATION OF THE a-Si:H DLTS AND ICTS EXPERIMENTAL DATA Ru-Qi Han, K.L. Ngai and J. Ruvalds	161
CAPACITANCE-VOLTAGE CHARACTERISTICS OF METALLIC GATE/OXIDE/a-Si:H MOS STRUCTURES Ruud E.I. Schropp, Jan Snijder and Jan F. Verwey	167
THE MEYER-NELDEL RELATION AND ANALYSIS OF THE FIELD-EFFECT IN AMORPHOUS SILICON Ruud E.I. Schropp, Jan Snijder and Jan F. Verwey	173

TRANSPORT MEASUREMENTS IN LPCVD AMORPHOUS SILICON OBTAINED FROM DISILANE C. Manfredotti, G. Gervino, L. Montaldi, U. Nastasi, R. Murri and L. Schiavulli	179
DENSITY-OF-STATES DISTRIBUTION IN DISILANE LPCVD DEPOSITED AMORPHOUS SILICON AS DETERMINED BY SCLC C. Manfredotti, G. Gervino, L. Montaldi, R. Varesio, A. Zanini and U. Nastasi	185
THICKNESS DEPENDENCE OF THE OPTICAL AND ELECTRICAL PROPERTIES OF THIN a-Si:H FILMS F. Demichelis, E. Mezzetti, P. Mpawenayo, A. Tagliaferro, E. Tresso, S. Bourquard, P. Rava, G. Della Mea and P. Mazzoldi	191
FREQUENCY-DEPENDENT NOISE IN HYDROGENATED AMORPHOUS SILICON F.Z. Bathaei and J.C. Anderson	197
DOPANT INCORPORATION AND DOPING EFFICIENCY IN a-Si:H AND a-Ge:H Martin Stutzmann	203
INCREASED CONDUCTIVITY IN P-TYPE HYDROGENATED AMORPHOUS SILICON Jacques I. Pankove and Joseph Dresner	209

PART III: PHOTO-INDUCED DEFECTS

CAPACITANCE STUDIES OF METASTABLE DEFECT CREATION IN HYDROGENATED AMORPHOUS SILICON J.D. Cohen, K. Mahavadi, K. Zellama, J.P. Harbison and A.E. Delahoy	213
TIME DEPENDENCE OF THE METASTABLE, OPTICALLY-INDUCED ESR IN a-Si:H C. Lee, W.D. Ohlsen and P.C. Taylor	225
THE EFFECT OF LIGHT SOAKING ON THE PHOTOCONDUCTIVITY RESPONSE IN a-Si:H Qui Changhua, Wu Wenhao, Zhao Shifu and Han Daxing	231
MEASUREMENTS OF LIGHT-INDUCED DEGRADATION IN a-Si,Ge:H,F ALLOYS J. Kolodzey, S. Aljishi, Z E. Smith, V. Chu, R. Schwartz and S. Wagner	237

PART IV: ALLOYS

DEPOSITION KINETICS AND STRUCTURAL CONTROL OF HIGHLY PHOTOSENSITIVE a-SiGe:H ALLOYS K. Tanaka and A. Matsuda	245
STATUS OF AMORPHOUS SILICON AND RELATED ALLOYS PREPARED BY PHOTOCHEMICAL VAPOR DEPOSITION Makoto Konagi	257
ELECTRONIC TRANSPORT AND THE DENSITY OF STATES DISTRIBUTION IN a-(Si,Ge):H,F ALLOYS S. Aljishi, Z E. Smith, D. Slobodin, J. Kolodzey, V. Chu, R. Schwarz and S. Wagner	269

a-(Si,Ge):H,F ALLOYS PREPARED FROM SiH ₄ AND GeF ₄ D. Slobodin, S. Aljishi, Y. Okada, D.-S. Shen, V. Chu and S. Wagner	275
FLOURINE INCORPORATION AND ANNEALING PROPERTIES OF a-Si,Ge:H,F ALLOYS STUDIED BY ELASTIC PROTON SCATTERING AND IR ABSORPTION R. Schwarz, Y. Okada, S.F. Chou, J. Kolodzey, D. Slobodin and S. Wagner	283
INFRARED SPECTROSCOPY OF DEUTERATED a-Si,Ge:D,F ALLOYS PREPARED BY DC GLOW DISCHARGE DEPOSITION Y. Okada, D. Slobodin, S.F. Chou, R. Schwarz and S. Wagner	289
INTERNAL PHOTOEMISSION MEASUREMENTS FOR THE DETERMINATION OF SCHOTTKY BARRIER HEIGHT ON a-Si,Ge:H,F ALLOYS V. Chu, S. Aljishi, D. Slobodin and S. Wagner	295
MICROCRYSTALLINITY IN a-Si,Ge:H,F ALLOYS D.S. Shen, J. Kolodzey, D. Slobodin, J.P. Conde, C. Lane, I.H. Campbell, P.M. Fauchet and S. Wagner	301
DEUTERON MAGNETIC RESONANCE IN a-Si and a-SiGe PRODUCED FROM FLOURIDES V.P. Bork, P.A. Fedders, R.E. Norberg, D.J. Leopold, K.D. Mackenzie and W. Paul	307
NMR AND ESR STUDIES ON a-Si _{1-x} Ge _x :H FILMS PREPARED BY GLOW DISCHARGE AND MAGNETRON SPUTTERING T. Shimizu, M. Kumeda, A. Morimoto, Y. Tsujimura and I. Kobayashi	313
PROPERTIES AND LOCAL STRUCTURE OF PLASMA-DEPOSITED AMORPHOUS SILICON-CARBON ALLOYS W.C. Mohr, C.C. Tsai and R.A. Street	319
GLOW DISCHARGE PRODUCED AMORPHOUS SiC:H THIN FILMS N.T. Tran, D.J. Olsen, R.I. Patel and K.A. Epstein	325
EFFECTIVE p ⁺ -DOPING OF a-Si:H AND a-SiC:H LAYERS BY PLASMA ASSISTED BORON DIFFUSION H.-D. Mohring, G.H. Bauer, G. Bilger and C.E. Nebel	331
A ²⁹ Si-NMR INVESTIGATION OF AMORPHOUS HYDROGENATED SILICON NITRIDE Mark A. Petrich, Rhett E. Livengood, Jeffrey A. Reimer and Dennis W. Hess	337
PHOTOELECTRONIC PROPERTIES OF a-Si:Se _x AND a-Si:Te _x THERMALLY EVAPORATED FILMS F.G. Wakim	343

PART V: INTERFACES

PROPERTIES OF THE INTERFACE BETWEEN AMORPHOUS SILICON AND NITRIDE C.C. Tsai, R.A. Street, F. Ponce and G.B. Anderson	351
IN SITU STUDIES OF THE MICROSTRUCTURE OF a-Si:H SURFACES AND INTERFACES R.W. Collins	361

THE ORIGIN OF SLOW STATES AT THE INTERFACE OF a-Si:H AND SILICON NITRIDE R.A. Street and C.C. Tsai	367
CHARACTERIZATION OF a-Si:H NEAR a-SiN _x :H/a-Si:H INTERFACE BY PHOTOLUMINESCENCE SPECTRA Tetsuzo Yoshimura, Kouichi Hiranaka, Tadahisa Yamaguchi, Shintaro Yanagisawa and Kunihiko Asama	373
OHMIC AND QUASI-OHMIC CONTACTS TO HYDROGENATED AMORPHOUS SILICON THIN FILMS J. Kanicki and D.B. Bullock	379
UHV INTERFACE STUDIES OF PALLADIUM SILICIDE FORMATION ON HYDROGENATED AMORPHOUS SILICON FILMS H.E. Rhodes, G. Apai, L. Rivaud, L.S. Hung and J.W. Mayer	387
TRANSPORT PROPERTIES OF AMORPHOUS SILICON/SILICON OXIDE HETEROSTRUCTURES H. Steemers, J. Mort, I. Chen, F. Jansen, S. Grammatica and D. Kuhman	393
THE PHOTOSENSITIVITY OF a-Si:H/P ⁺ Pc-Si HETEROJUNCTION Wanlu Wang and Kejun Liao	399

PART VI: SUPERLATTICES

AMORPHOUS SILICON-BASED SUPERLATTICES AND THEIR POTENTIALS TO DEVICE APPLICATIONS Masataka Hirose, Naoki Murayama, Seiichi Miyazaki and Yohji Ihara	405
OPTOELECTRONIC PROPERTIES OF A-GE:H/A-SI:H SUPERLATTICE STRUCTURES C.R. Wronski, P.D. Persans, B. Abeles, T. Tiedje and M. Hicks	415
THE EFFECT OF DEPOSITION PROCEDURE ON THE CONDUCTIVITY OF HYDROGENATED AMORPHOUS SILICON MULTILAYER FILMS G. Moddel, F.-C. Su and P.E. Vanier	423
ELECTRONIC AND HOLE TRANSPORT PERPENDICULAR TO THE PLANES OF a-Si:H/a-Si,Ge:H COMPOSITIONAL SUPERLATTICES J. Kolodzey, S. Aljishi, R. Schwarz, D.-S. Shen, S. Quinlan, S.A. Lyon and S. Wagner	429
CARRIER SEPARATION EFFECTS IN DOPING MODULATED AMORPHOUS SILICON J. Kakalios, C.C. Tsai and R.A. Street	435
ORIGIN OF PERSISTENT PHOTOCONDUCTIVITY IN MODULATION DOPED AMORPHOUS SILICON MULTILAYERS S.C. Agarwal and S Guha	441
PARAMETERS AFFECTING LIGHT-INDUCED EXCESS CONDUCTIVITY IN AMORPHOUS SILICON DOPING-MODULATED MULTILAYERS F.-C. Su, S. Levine and P.E. Vanier	447

PART VII: SOLAR CELLS

RECENT ADVANCES IN a-Si SOLAR CELL TECHNOLOGY IN JAPAN Y. Kuwano	455
IMPURITIES AND METASTABLE CENTERS IN AMORPHOUS SILICON SOLAR CELLS D.E. Carlson	467
STATUS OF FLUORINATED AMORPHOUS SILICON ALLOY MULTI-JUNCTION SOLAR CELLS Jeffrey Yang, Robert Ross, Ralph Mohr and Jeffrey P. Fournier	475
a-Si BASIS HETEROJUNCTION STACKED SOLAR CELLS Y. Hamakawa, Y. Matsumoto, Xu Zhang-Yang, M. Okuyama, H. Takakura and H. Okamoto	481
FABRICATION OF THE LARGE-AREA INTEGRATED a-Si SOLAR CELLS S. Yamazaki, M. Abe, S. Nagayama, K. Shibata, M. Susukida, T. Fukada, M. Kinka, I. Kobayashi, T. Inushima and K. Suzuki	487
a-SiGe:H ALLOY AND ITS APPLICATION TO TANDEM-TYPE SOLAR CELL Y. Yukimoto and M. Aiga	493
INTEGRATED SERIES CONNECTION OF a-Si:H SOLAR CELLS W. Juergens, H. Kausche, W. Peters and W. Stetter	501
HIGH QUALITY a-Si FILMS AND SUPERLATTICE STRUCTURE p-LAYER a-Si SOLAR CELLS S. Nakano, S. Tsuda, H. Tarui, T. Takahama, H. Haku, K. Watanabe, M. Nishikuni, Y. Hishikawa and Y. Kuwano	511
EFFECT OF SUPERLATTICE DOPED LAYERS ON THE PERFORMANCE OF a-Si:H P-I-N SOLAR CELLS Rajeewa R. Arya, Anthony Catalano and James O'Dowd	517
ASYMMETRIES IN AMORPHOUS SILICON DEVICES Z E. Smith and S. Wagner	525
THE EFFECTS OF DOPANT PROFILES ON THE DEVICE PARAMETERS OF p-i-n AND n-i-p a-Si SOLAR CELLS F.R. Jeffrey, G.D. Vernstrom, M. Weber and K.A. Epstein	531
OBSERVATION AND STUDY OF WAVELENGTH DEPENDENCE OF THE OPEN-CIRCUIT VOLTAGE IN a-Si:H BASED p-i-n SOLAR CELLS M. Gorn, N. Kniffler and G. Winterling	537
TEMPERATURE AND LIGHT INTENSITY DEPENDENCES OF OPEN CIRCUIT VOLTAGE IN a-Si:H PIN SOLAR CELLS Jin Jang and Choochon Lee	543
TRANSIENT BEHAVIOR OF PHOTOCURRENT IN a-Si:H SOLAR CELLS Gao Guang, Miao Quinghai, Cao Baocheng, Guo Xiaoqin and Dai Guocai	549
WAVELENGTH DEPENDENCE OF THE TURN-OFF CHARACTER IN a-Si:H SOLAR CELLS Miao Quinghai, Gao Guang, Cao Baocheng and Dai Guocai	553

EXPERIMENTAL AND THEORETICAL RESULTS FOR LIGHT TRAPPING IN HIGH EFFICIENCY a-Si _{1-x} C _x :H/a-Si:H SOLAR CELLS PREPARED ON GRANULAR TIN OXIDE	
F.B. Ellis, Jr., A.E. Delahoy, M. Böhm, J.A. Cambridge and T. Horning	557
INFLUENCE OF TRANSPARENT CONDUCTING OXIDE ON AMORPHOUS SILICON SOLAR CELL PERFORMANCE	
Chris Walker, Russell Hollingsworth, Joe del Cueto and Arun Madan	563
PROPERTIES OF INDIUM TIN OXIDE FILMS PREPARED USING REACTIVE RF MAGNETRON SPUTTERING	
Madhav Mehra and Howard Rhodes	569
PART VIII: SOLAR-CELL STABILITY	
LIGHT INDUCED EFFECTS IN a-Si:H FILMS AND SOLAR CELLS	
Y. Uchida and H. Sakai	577
STABILITY OF AMORPHOUS SILICON SOLAR CELLS -- NEW TANDEM a-SiC/a-Si SOLAR CELLS	
Y. Tawada, J. Takada, M. Yamaguchi, H. Yamagishi, Y. Hosokawa, A. Hiroe, M. Kondo, K. Asaoka, N. Fukada and K. Tsuge	587
EFFECTS OF LIGHT SOAKING CONDITIONS ON THIN FILM SILICON: HYDROGEN ALLOY SOLAR CELLS	
D.R. Willett, D.P. Tanner and G. McHenry	599
STABILITY AND EFFICIENCY IN AMORPHOUS TANDEM SOLAR CELLS	
F. Galluzzi, G. Conte, L. De Angelis and R. Peruzzi	605
PART IX: THIN-FILM TRANSISTORS AND DISPLAYS	
THE MATERIALS ISSUES AND APPLICATIONS OF AMORPHOUS SILICON THIN FILM TRANSISTORS	
M.J. Thompson	613
AMORPHOUS SILICON ALLOY TECHNOLOGY FOR ACTIVE MATRIX DISPLAYS	
Z. Yaniv, V. Cannella, Y. Baron, A. Lien and J. McGill	625
VLSI PROCESSING OF AMORPHOUS SILICON ALLOY p-i-n DIODES FOR ACTIVE MATRIX APPLICATIONS	
J. McGill, V. Cannella, Z. Yaniv, P. Day and M. Vijan	637
DOUBLE INJECTION FIELD EFFECT TRANSISTOR: A NEW TYPE OF SOLID STATE DEVICE	
M. Hack, M. Shur and W. Czubytyj	643
SHORT CHANNEL LENGTH PLANAR TFT's USING AMORPHOUS SILICON ALLOYS	
M. Yang, Z. Yaniv, M. Vijan and V. Cannella	647
NOVEL a-Si:H THIN FILM HIGH VOLTAGE TRANSISTOR	
H.C. Tuan	651
APPLICATION OF TWO-STEP DEPOSITION METHOD TO ULTRA-THIN a-Si FETs	
Y. Katoh, O. Sugiura, Y. Takeuchi, Y. Uchida and M. Matsumura	657

BACK-TO-BACK AMORPHOUS SILICON DIODES FOR DRIVING LC DISPLAYS
Joseph Dresner 663

PART X: PHOTORECEPTORS AND IMAGE SENSORS

ELECTROPHOTOGRAPHIC PROPERTIES OF n^+ -a-Si:H/a-Si:H/a-SiC:H
HETEROSTRUCTURES
S.M. Paasche and G. H. Bauer 671

THIN MULTI-LAYERED PHOTORECEPTOR DEPOSITED FROM DISILANE
S. Araki, H. Nou, H. Kamaji and K. Kiyota 677

a-Si:H IMAGE SENSORS: SOME ASPECTS OF PHYSICS AND PERFORMANCE
K. Rosan and G. Brunst 683

INFLUENCE OF UNSYMMETRICAL ELECTRODE STRUCTURE ON a-Si
PHOTODIODE CHARACTERISTICS
M. Hayama, K. Kobayashi, H. Miki and Y. Onishi 689

PART XI: OPTICAL DATA STORAGE

TELLURIUM ALLOYS FOR REVERSIBLE OPTICAL DATA STORAGE
R.T. Young, D. Strand, J. Gonzalez-Hernandez and S.R. Ovshinsky 697

THE OPTICAL PROPERTIES AND STABILITY OF Ge AND Sn-DOPED
TeO_x FILMS
W.-Y. Lee, C.R. Davis, G. Lim, H. Coufal and F. Sequeda 705

CRYSTALLIZATION RATE AND THERMAL STABILITY OF Te-BASED ALLOY
THIN FILMS FOR ERASABLE OPTICAL RECORDING
R.C. Ross, D.A. Strand, E.J. Bjornard and J.P. DeNeufville 713

OPTICAL RESPONSE OF As₂S₃: MELT QUENCHED VERSUS SPIN CASTED
MATERIALS
M. Hamman and J.J. Santiago 719

PART XII: LATE PAPER ACCEPTANCE

PLANAR AND PERPENDICULAR CONDUCTIVITY OF DOPING MODULATED
AMORPHOUS SILICON MULTILAYERS
H. Steemers, I. Chen, J. Mort, F. Jansen, M. Morgan,
M. Machonkin and D. Kuhman 727

AUTHOR INDEX 733

SUBJECT INDEX 737